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Part 503-3: Quality assessment – Measuring method of contact resistance for the printed thin film transistor – Transfer length method

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CONTENTS

FOREWORD 3
INTRODUCTION 5
1 Scope 6
2 Normative references 6
3 Terms and definitions 6
4 Symbols and abbreviated terms 7
5 Measuring method of contact resistance 8
5.1 General 8
5.2 Preparation of TEGs 8
5.3 Measuring apparatus 9
5.4 Environmental conditions and storage 9
5.5 Measuring procedure 9
5.6 Data analysis 10
5.6.1 Calculation procedure of normalized resistances for each TEG 10
5.6.2 Derivation procedure of contact resistance (R_C) 10
5.7 Report 11
Annex A (informative) Examples of sets of source and drain electrodes layouts in a TEG 12
Bibliography 13

Figure 1 – Schematic structure of printed thin film transistors (TFTs) 7
Figure 2 – Measurement configuration 8
Figure 3 – Example of plots of the total resistance R versus the distance between the source and drain electrode (channel length) L 10
Figure A.1 – Example of a set of source and drain electrodes in a TEG 12

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The language used for the development of this International Standard is English.

This document was drafted in accordance with ISO/IEC Directives, Part 2, and developed in accordance with ISO/IEC Directives, Part 1 and ISO/IEC Directives, IEC Supplement, available at www.iec.ch/members_experts/refdocs. The main document types developed by IEC are described in greater detail at www.iec.ch/standardsdev/publications.

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INTRODUCTION

In a thin film transistor (TFT), contact resistance occurs at the contacting interfaces at the gate, source and drain electrodes, and the TFT semiconductor layer. While contact resistance is negligible at the gate electrode, it reduces the effective voltage applied to the source and drain electrodes. Therefore, the evaluation of the contact resistance can provide important insights related to the performance characteristics of printed TFTs. Especially for printed electronics, the contact resistance varies with the employed materials, printing processes and the time series variation because the interface is made of simple contact obtained by additive manufacturing instead of a junction obtained by vacuum deposition and etching processes. Thus, the performance of printed TFTs is greatly influenced by the value of contact resistance. A change of the contact resistance is therefore considered to be a key factor for a proper interpretation of performance, lifetime, and reliability of a printed TFT.

To determine the contact resistance, several techniques, including but not limited to two-terminal contact method, four-terminal contact method, six-terminal contact method, transfer length method, and scanning probe potentiometer technique can be used. The transfer length method (TLM) in particular has a practical advantage because the supplier can test discrete devices, which have the same structure as the original printed TFT, on a common substrate simultaneously. Furthermore, the TLM is cost-effective because the user can measure the apparent contact resistance without using expensive equipment. Therefore, by using TLM, the supplier and the user can exchange the important parameter of the TFT that is contact resistance for reliability assessment as a part of their supply chain service.

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1 Scope

This part of IEC 62899 specifies a measuring method of contact resistance for printed thin film transistors (TFTs) by the transfer length method (TLM). The method requires the fabrication of a test element group (TEG) with varying channel length (L) between source and drain electrodes. The method is intended for quality assessment of TFT electrode contacts and is suited for determining whether the contact resistance lies within a desired range.

2 Normative references

There are no normative references in this document.